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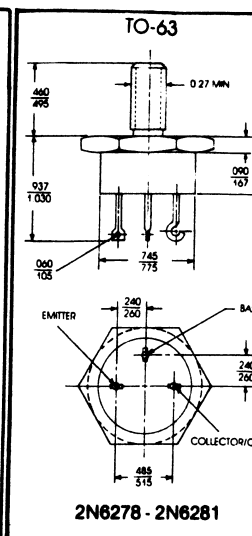
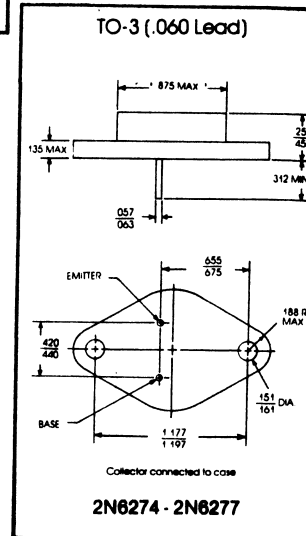
NPN POWER TRANSISTORS 50 AMP SWITCHING

2N6274 thru
2N6281

- 250 W. Continuous Power
- VCEO (sus) to 150 V.

MAXIMUM RATINGS

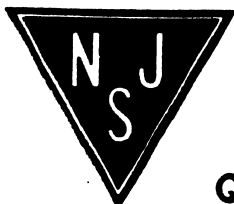
PARAMETER	SYMBOL	2N6274	2N6275	2N6276	2N6277	UNIT
		2N6278	2N6279	2N6280	2N6281	
Collector-Emitter Voltage	V _{CEO}	100	120	140	150	V
Collector-Base Voltage	V _{CBO}	120	140	160	180	V
Emitter-Base Voltage	V _{EBO}	6	6	6	6	V
Collector Current-Continuous		50	50	50	50	A
-Peak		100	100	100	100	A
Base Current-Continuous		20	20	20	20	A
Power Dissipation @ T _c < 25°C		250	250	250	250	W
Linear Derating Factor		1.43	1.43	1.43	1.43	W/°C
Storage & Operating Junction Temp. Range		-65°C to +200°C				
Lead Temperature (1/16" from case)		+235°C for 10 seconds				



ELECTRICAL CHARACTERISTICS AT 25°C CASE TEMPERATURE

PARAMETER	SYMBOL	TEST CONDITIONS	2N6274 2N6278		2N6275 2N6279		2N6276 2N6280		2N6277 2N6281		UNIT
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Collector Cutoff Current	I _{CEX}	^{1,2} V _{CE} = 120V, V _{BE} = 1.5V		1		1					mA
		² V _{CE} = 140V, V _{BE} = 1.5V				1					mA
		² V _{CE} = 160V, V _{BE} = 1.5V					1				mA
		² V _{CE} = 180V, V _{BE} = 1.5V						1			mA
Collector Cutoff Current	I _{CEX}	¹ V _{CE} = 120V, V _{BE} = 1.5V		10						1	μA
		V _{CE} = 140V, V _{BE} = 1.5V				10					μA
		V _{CE} = 160V, V _{BE} = 1.5V					10				μA
		V _{CE} = 180V, V _{BE} = 1.5V						10			μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 6V		100		100		100		100	μA
Collector-Emitter Sustain Voltage*	V _{CEO(sus)}	I _B = 0, I _C = 50mA	100		120		140		150		V
DC Forward Current Transfer Ratio*	h _{FE}	V _{CE} = 4V, I _C = 50A	10		10		10		10		
		V _{CE} = 4V, I _C = 20A	30	120	30	120	30	120	30	120	
		V _{CE} = 4V, I _C = 1A	50		50		50		50		
Collector-Emitter Saturation Voltage*	V _{CE(sat)}	I _C = 50A, I _B = 10A		3		3		3		3	V
		I _C = 20A, I _B = 2A		1		1		1		1	V
Base-Emitter Voltage*	V _{BE(sat)}	I _C = 50A, I _B = 10A		1.2		1.2		1.2		1.2	V
		I _C = 20A, I _B = 2A		1.8		1.8		1.8		1.8	V
Base Emitter On Voltage	V _{BE(on)}	I _C = 20A, V _{CE} = 4V		1.8		1.8		1.8		1.8	V
Collector Cutoff Current	I _{CEO}	V _{CE} = 50V, I _B = 0		50							μA
		V _{CE} = 60V, I _B = 0				50					μA
		V _{CE} = 70V, I _B = 0					50				μA
		V _{CE} = 75V, I _B = 0						50			μA
Rise Time	t _r	V _{CC} = 80V, I _C = 20A I _{B1} = 2A, V _{OB} = 5V		.35		.35		.35		.35	μs
Storage Time	t _s	V _{CC} = 80V, I _C = 20A I _{B1} = I _{B2} = 2A		.80		.80		.80		.80	μs
High Frequency Beta	h _{fe}	V _{CE} = 10V, I _C = 1A, f = 10MHz	3		3		3		3		
Common Base Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 0.1MHz		600		600		600		600	pF

* Pulse Test: Pulse width < 300 μs; Duty Cycle < 2%
¹ Emitter diode is reverse biased
 2. T_c = 150°C



Quality Semi-Conductors